SCHOTTKY DIODE

SOT-563

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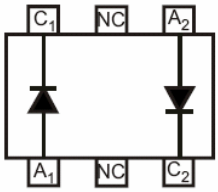
FEATURES

Surface mount schottky barrier diode arrays



Marking: KAV

Maximum Ratings @T_A=25℃

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	V
Average Rectified Output Current	I_O	200	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta}JA$	833	℃/W
Storage temperature	T_{STG}	-65-125	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	I_R= 100μA	30		V
Reverse voltage leakage current	I_R	V_R=25V		2	uA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=30mA I_F=100mA		320 400 500 1000	mV
Total capacitance	C_T	V_R=1V,f=1MHz		10	pF
Reverse recovery time	t_{rr}	I_F=10mA, I_R=10mA~1mA R_L=100Ω		5	nS

Typical Characteristics

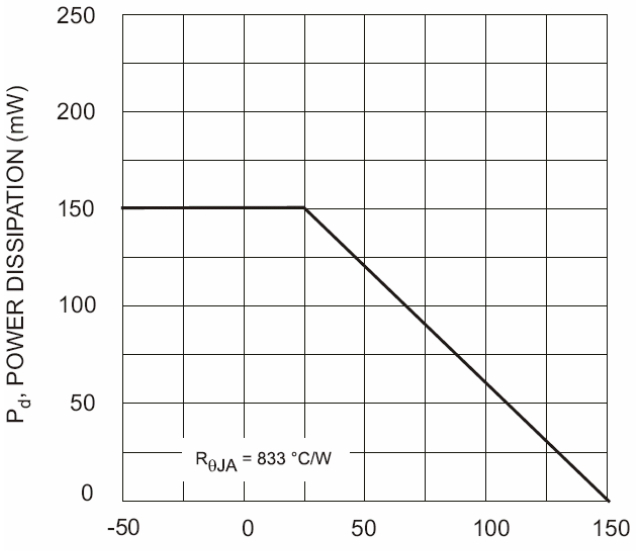


Fig. 1, Derating Curve - Total

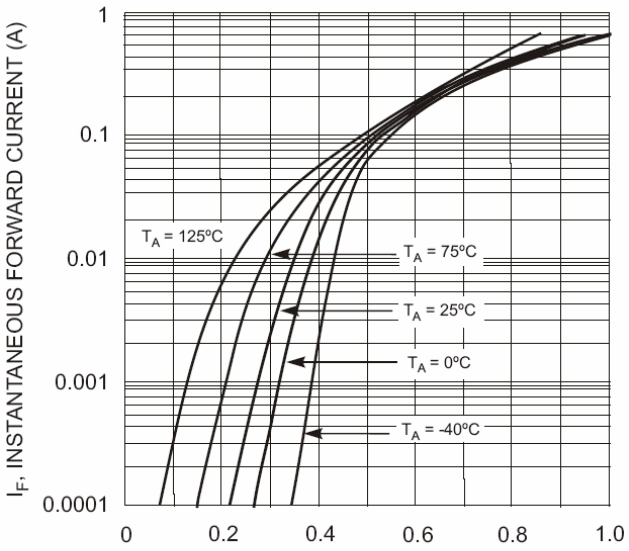


Fig. 2 Forward Characteristics

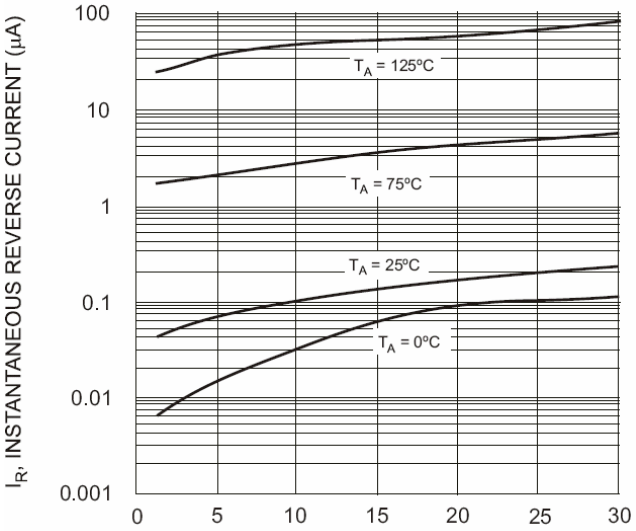


Fig. 3 Typical Reverse Characteristics

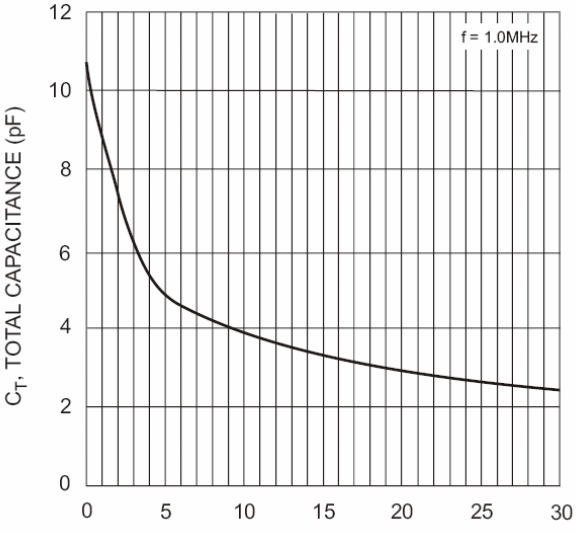


Fig. 4 Typical Capacitance vs. Reverse Voltage